Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	14546	((438/149) or (438/174) or (438/176) or (438/180) or (438/181) or (438/184) or (438/185) or (438/197) or (438/199) or (438/201) or (438/207) or (438/211) or (438/213) or (438/217) or (438/218) or (438/221) or (438/222) or (438/229) or (438/230) or (438/231) or (438/233) or (438/260) or (438/265) or (438/276) or (438/289) or (438/294) or (438/296) or (438/299) or (438/300) or (438/301) or (438/303) or (438/311) or (438/318) or (438/320) or (438/364) or (438/406) or (438/413) or (438/416) or (438/429) or (438/430) or (438/459) or (438/488) or (438/491) or (438/532) or (438/597) or (438/607) or (438/704)).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/11/29 10:48
L2	69788	soi or (silicon near2 insulator)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/11/29 10:49
L3	2565	1 and 2	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/11/29 10:49
L4	14	3 and (front and back) near5 gate	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/11/29 10:49

S1	13657	((438/149) or (438/174) or (438/176) or (438/180) or (438/181) or (438/184) or (438/185) or (438/197) or (438/199) or (438/201) or (438/207) or (438/211) or (438/213) or (438/217) or (438/218) or (438/221) or (438/222) or (438/229) or (438/230) or (438/231) or (438/233) or (438/260) or (438/265) or (438/276) or (438/289) or (438/294) or (438/296) or (438/299) or (438/300) or (438/301) or (438/303) or (438/311) or (438/318) or (438/320) or (438/364) or (438/406) or (438/413) or (438/416) or (438/429) or (438/430) or (438/459) or (438/488) or (438/491) or (438/532) or (438/597) or (438/607) or (438/704)).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/11/29 10:48
S2	31127	soi or (silicon near2 insulator)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/11/29 10:48
S3	109204	cmos or (complementary near (metal near2 oxide))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/07/31 20:31
S4	2814	simox or (separation adj ion adj implantation adj oxygen)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/07/31 20:32
S5	1333	(front and back) near5 gate	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/11/29 10:49
S6	154699	gate near5 (dielectric or insulat$3 or oxide)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/07/31 20:34
S7	85681	trench$2	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/07/31 20:34

S8	4	sacrifical near3 spacer$1	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/07/31 21:21
S9	10	sacrifical same spacer$1	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/07/31 20:35
S10	7641	(soi or (silicon near2 insulator)) and (cmos or (complementary near (metal near2 oxide)))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/07/31 20:36
S11	1178	((soi or (silicon near2 insulator)) and (cmos or (complementary near (metal near2 oxide)))) and (simox or (separation adj ion adj implantation adj oxygen))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/07/31 20:43
S12	32	(((soi or (silicon near2 insulator)) and (cmos or (complementary near (metal near2 oxide)))) and (simox or (separation adj ion adj implantation adj oxygen))) and ((front and back) near5 gate)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/07/31 20:43
S13	32	((((soi or (silicon near2 insulator)) and (cmos or (complementary near (metal near2 oxide)))) and (simox or (separation adj ion adj implantation adj oxygen))) and ((front and back) near5 gate))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/07/31 20:44
S14	0	((((((soi or (silicon near2 insulator)) and (cmos or (complementary near (metal near2 oxide)))) and (simox or (separation adj ion adj implantation adj oxygen))) and ((front and back) near5 gate)) and (gate near5 (dielectric or insulat$3 or oxide))) and trench$2) and (sacrifical same spacer$1)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/07/31 20:45
S15	16	(((((soi or (silicon near2 insulator)) and (cmos or (complementary near (metal near2 oxide)))) and (simox or (separation adj ion adj implantation adj oxygen))) and ((front and back) near5 gate)) and (gate near5 (dielectric or insulat$3 or oxide))) and trench$2	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/07/31 20:53

S16	1	((((((soi or (silicon near2 insulator)) and (cmos or (complementary near (metal near2 oxide)))) and (simox or (separation adj ion adj implantation adj oxygen))) and ((front and back) near5 gate)) and (gate near5 (dielectric or insulat$3 or oxide))) and trench$2) and (((438/149) or (438/174) or (438/176) or (438/180) or (438/181) or (438/184) or (438/185) or (438/197) or (438/199) or (438/201) or (438/207) or (438/211) or (438/213) or (438/217) or (438/218) or (438/221) or (438/222) or (438/229) or (438/230) or (438/231) or (438/233) or (438/260) or (438/265) or (438/276) or (438/289) or (438/294) or (438/296) or (438/299) or (438/300) or (438/301) or (438/303) or (438/311) or (438/318) or (438/320) or (438/364) or (438/406) or (438/413) or (438/416) or (438/429) or (438/430) or (438/459) or (438/488) or (438/491) or (438/532) or (438/597) or (438/607) or (438/704)).CCLS.)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/07/31 20:47
S17	9	("6074209" | "6275094" | "6359312" | "6383904" | "6391695" | "6392277" | "6423599" | "6432754" | "6441436").PN.	USPAT	OR	OFF	2004/07/31 21:11
S18	16	("3853633" | "4222062" | "4393578" | "4839707" | "4951123" | "5166765" | "5273921" | "5285352" | "5376578" | "5482871" | "5726459" | "5780912" | "6008126" | "6057555" | "6074920" | "6166412").PN.	USPAT	OR	OFF	2004/07/31 21:14
S19	9	("6074209" | "6275094" | "6359312" | "6383904" | "6391695" | "6392277" | "6423599" | "6432754" | "6441436").PN.	USPAT	OR	OFF	2004/07/31 21:17
S20	7	("5164805" | "5885887" | "6204138" | "6284594" | "6359298" | "6365450" | "6376312").PN.	USPAT	OR	OFF	2004/07/31 21:19

S21	350479	spacer$1	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/07/31 21:21
S22	9	("4601779" | "5273921" | "5296727" | "5461250" | "5497019" | "5604368" | "5681775" | "5929479" | "6248637").PN.	USPAT	OR	OFF	2004/07/31 21:23
S23	32	(((((soi or (silicon near2 insulator)) and (cmos or (complementary near (metal near2 oxide)))) and (simox or (separation adj ion adj implantation adj oxygen))) and ((front and back) near5 gate)) and (gate near5 (dielectric or insulat$3 or oxide))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/07/31 21:28
S24	4	("5291047" | "5446299" | "5488243" | "5751037").PN.	USPAT	OR	OFF	2004/07/31 21:31
S25	19	"5929479".URPN.	USPAT	OR	OFF	2004/07/31 21:32